**IN THE UNITED STATES PATENT AND TRADEMARK OFFICE**

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| In re Application of: | | ) | PATENT APPLICATION |
| Inventors: | Jong-Jan Lee, Sheng Teng Hsu, Douglas J. Tweet and Jer-Shen Maa | ) | |
| Serial No.: | Not Yet Assigned | ) | Attorney Docket No. SLA 0733 |
| Filed: | Herewith | ) | |
| Title: | STRAINED SILICON finFET DEVICE | ) | |

Honorable Commissioner for Patents
Washington, D.C. 20231

INFORMATION DISCLOSURE STATEMENT UNDER 37 C.F.R. §1.97

Sir:

Listed on attached Form PTO-1449 is information submitted pursuant to 37 C.F.R. §1.56. A copy of each listed publication is submitted herewith.

Applicant respectfully requests that the listed information be considered by the Examiner and made of record in the above-identified application.

(Date) 6/23/03

Respectfully submitted,

David C. Ripma
Reg. No. 27,672

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PTO/SB/08A (10-01)
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U.S. Patent and Trademark Office: U.S. DEPARTMENT OF COMMERCE


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# INFORMATION DISCLOSURE STATEMENT BY APPLICANT

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Sheet 1 of 3

| Complete if Known | |
|---|---|
| Application Number | |
| Filing Date | 06-23-03 |
| First Named Inventor | Jong-Jan Lee |
| Art Unit | |
| Examiner Name | |
| Attorney Docket Number | SLA0733 |

## U.S. PATENT DOCUMENTS

| Examiner Initials* | Cite No.[1] | Document Number: Number - Kind Code[2] (if known) | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear |
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| Examiner Initials* | Cite No.[1] | Foreign Patent Document: Country Code[3] - Number[4] - Kind Code[5] (if known) | Publication Date MM-DD-YYYY | Name of Patentee or Applicant of Cited Document | Pages, Columns, Lines, Where Relevant Passages or Relevant Figures Appear | T[6] |
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Sheet 2 of 3

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| Application Number | |
| Filing Date | 06-23-03 |
| First Named Inventor | Sheng Teng Hsu |
| Group Art Unit | |
| Examiner Name | |
| Attorney Docket Number | SLA0733 |

## OTHER PRIOR ART -- NON PATENT LITERATURE DOCUMENTS

| Examiner Initials* | Cite No.[1] | Include name of the author (in CAPITAL LETTERS), title of the article (when appropriate), title of the item (book, magazine, journal, serial, symposium, catalog, etc.), date, page(s), volume-issue number(s), publisher, city and/or country where published. | T[2] |
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|---|---|---|---|
| | | X. HUANG, W-C. LEE, C. KUO, D. HISAMOTO, L. CHANG, J. KEDZIERSKI, E. ANDERSON, H. TAKEUCHI, Y-K. CHOI, K. ASANO, V. SUBRAMANIAN, T-J. KING, J. BOKOR, C. HU, *Sub 50-nm p-channel finFET,* IEEE Transactions on Electron Devices, Vol. 48, No. 5, May 2001, pp. 880-886. | |
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